

# DIGITRON SEMICONDUCTORS

## 2N489-2N494, A, B

## NPN SILICON UNIJUNCTION TRANSISTOR

Silicon unijunction transistors are three-terminal device having a stable "N" type negative resistance characteristic over a wide temperature range.

### FEATURES

- Stable operation over wide temperature range
- Low leakage current
- Low peak point current
- Guaranteed minimum pulse voltage
- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

### MAXIMUM RATINGS

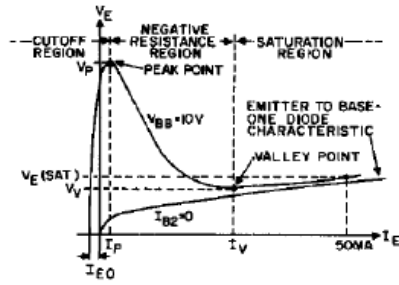
Rating	Value
Total RMS Power Dissipation (Unstabilized)	450mW
Total RMS Power Dissipation (Stabilized)	600mW
RMS Emitter Current	70mA
Peak Emitter Current ( $T_J = 150^\circ\text{C}$ )	2 A
Emitter Reverse Voltage ( $T_J = 150^\circ\text{C}$ )	60 V
Operating Temperature Range	$-65^\circ$ to $+140^\circ\text{C}$
Operating Temperature Range (Stabilized)	$-65^\circ$ to $+175^\circ\text{C}$
Storage Temperature Range	$-65^\circ$ to $+175^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

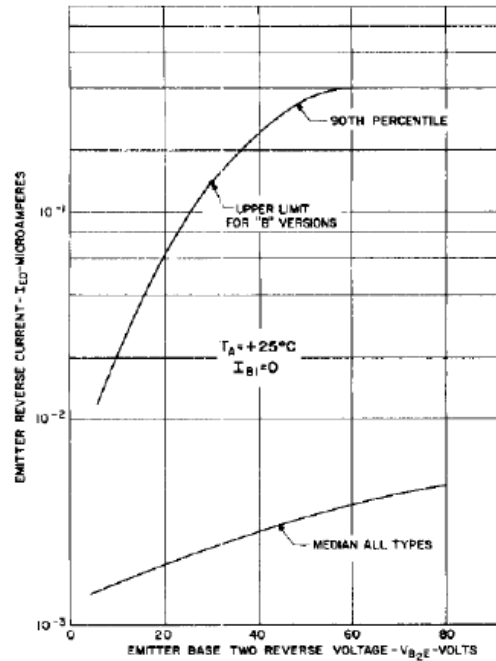
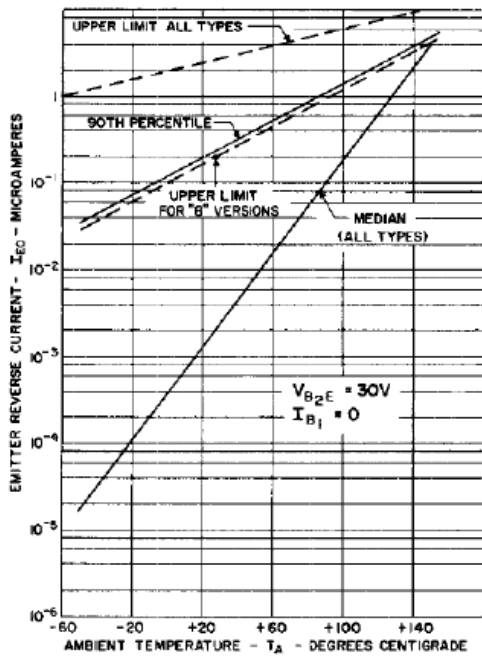
Part number	Intrinsic standoff ratio <sup>(1)</sup>		Interbase resistance <sup>(2)</sup>		Modulated interbase current		Maximum				Minimum		Base one peak pulse voltage		
	$V_{RR} = 10\text{V}$		$V_{BB} = 3\text{V}$		$I_R = 50\text{mA}$ $V_{BB} = 10\text{V}$		Emitter saturation voltage	Emitter reverse current		Peak point current	Valley point current	$R_{B2} = 100\Omega$ $V_{BB} = 20\text{V}$			
			$R_{BBO}$		$I_{B2(MOI)}$		$V_{E(SAT)}$	$I_{EB2O}$	$T_J = 150^\circ\text{C}$ $V_{B2E} = 10\text{V}$	$V_{B2E} = 30\text{V}$	$V_{BB} = 25\text{V}$			$I_V$	
	$\eta$		k $\Omega$		mA		Volts	$\mu\text{A}$	$\mu\text{A}$	$\mu\text{A}$	$\mu\text{A}$			mA	Volts
	Min	Max	Min	Max	Min	Max									
2N489	.51	.62	4.7	6.8	6.8	22	5	2	20	-	12	8	-		
2N489A	.51	.62	4.7	6.8	6.8	22	4	2	20	-	12	8	3		
2N489B	.51	.62	4.7	6.8	6.8	22	4	2	20	0.2	6	8	3		
2N490	.51	.62	6.2	9.1	6.8	22	5	2	20	-	12	8	-		
2N490A	.51	.62	6.2	9.1	6.8	22	4	2	20	-	12	8	3		
2N490B	.51	.62	6.2	9.1	6.8	22	4	2	20	0.2	6	8	3		
2N490C	.51	.62	6.2	9.1	6.8	22	4	2	20	0.02	2	8	3		
2N491	.56	.68	4.7	6.8	6.8	22	5	2	20	-	12	8	-		
2N491A	.56	.68	4.7	6.8	6.8	22	4.3	2	20	-	12	8	3		
2N491B	.56	.68	4.7	6.8	6.8	22	4.3	2	20	0.2	6	8	3		
2N492	.56	.68	6.2	9.1	6.8	22	5	2	20	-	12	8	-		
2N492A	.56	.68	6.2	9.1	6.8	22	4.3	2	20	-	12	8	3		
2N492B	.56	.68	6.2	9.1	6.8	22	4.3	2	20	0.2	6	8	3		
2N492C	.56	.68	6.2	9.1	6.8	22	4.3	2	20	0.02	2	8	3		
2N493	.62	.75	4.7	6.8	6.8	22	5	2	20	-	12	8	-		
2N493A	.62	.75	4.7	6.8	6.8	22	4.6	2	20	-	12	8	3		
2N493B	.62	.75	4.7	6.8	6.8	22	4.6	2	20	0.2	6	8	3		
2N494	.62	.75	6.2	9.1	6.8	22	5	2	20	-	12	8	-		
2N494A	.62	.75	6.2	9.1	6.8	22	4.6	2	20	-	12	8	3		
2N494B	.62	.75	6.2	9.1	6.8	22	4.6	2	20	0.2	6	8	3		
2N494C	.62	.75	6.2	9.1	6.8	22	4.6	2	20	0.02	2	8	3		

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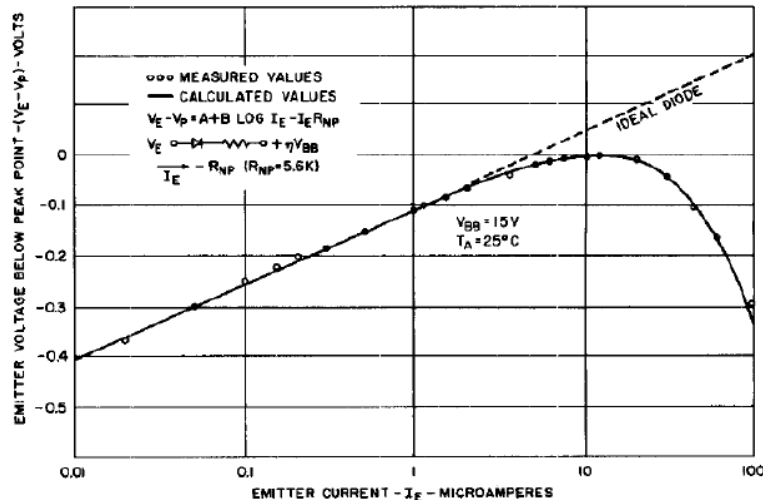
## 2N489-2N494, A, B      NPN SILICON UNIJUNCTION TRANSISTOR



Static emitter characteristic curves showing important parameters and measurement points.



Emitter reverse current characteristics

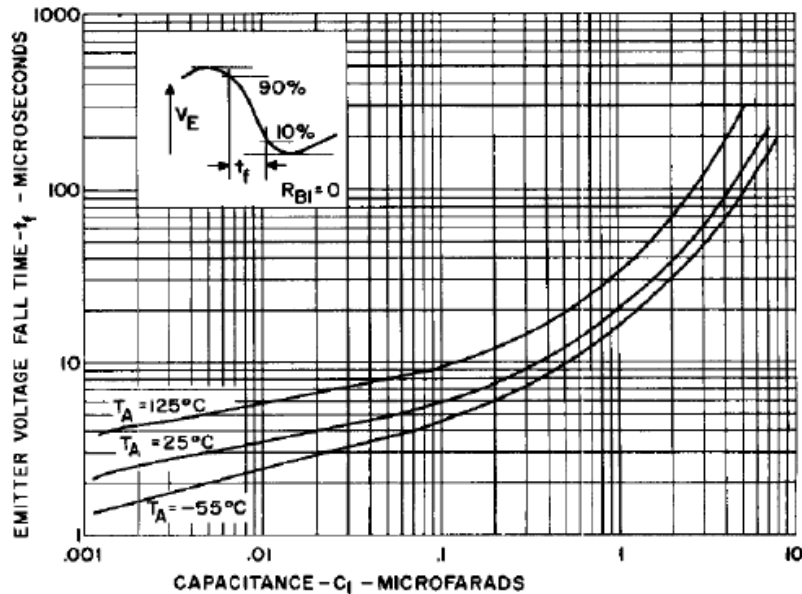


Static emitter characteristics at peak point

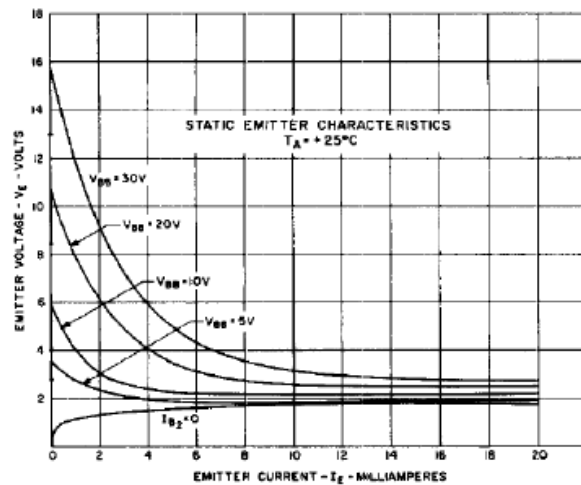
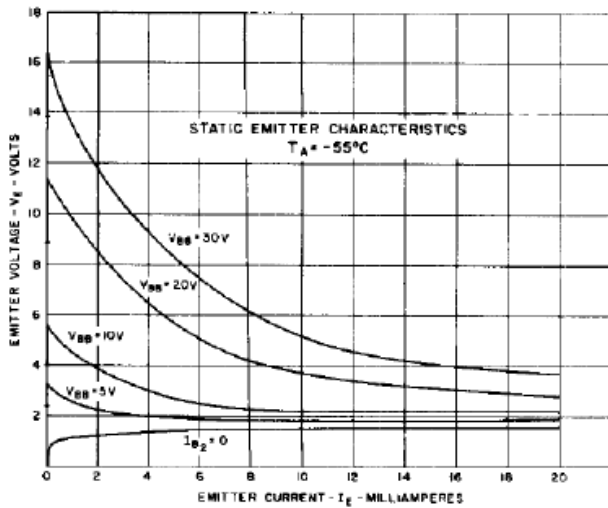
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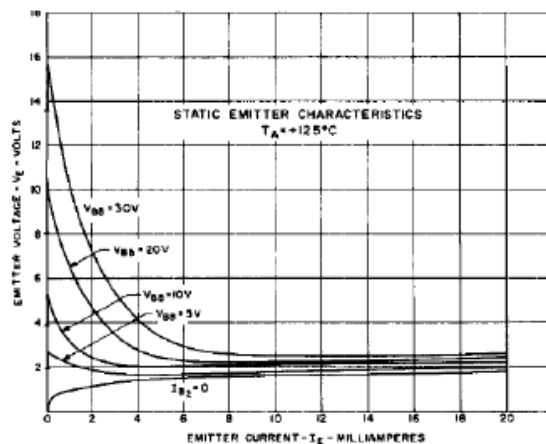
NPN SILICON UNIJUNCTION TRANSISTOR



Emitter voltage fall time vs. capacitance in relaxation oscillator



Static emitter characteristics

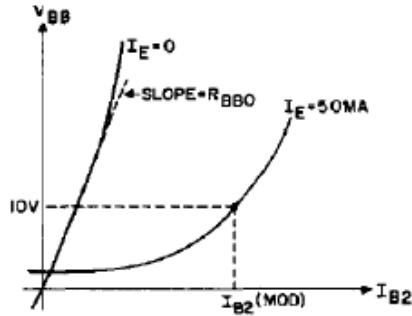


Static emitter characteristics

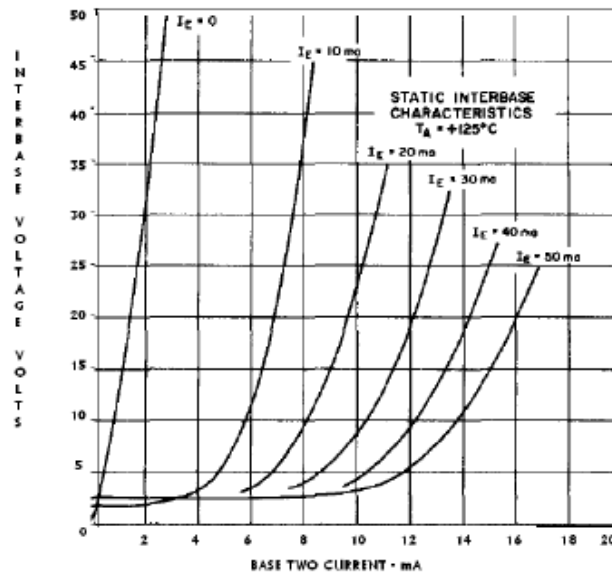
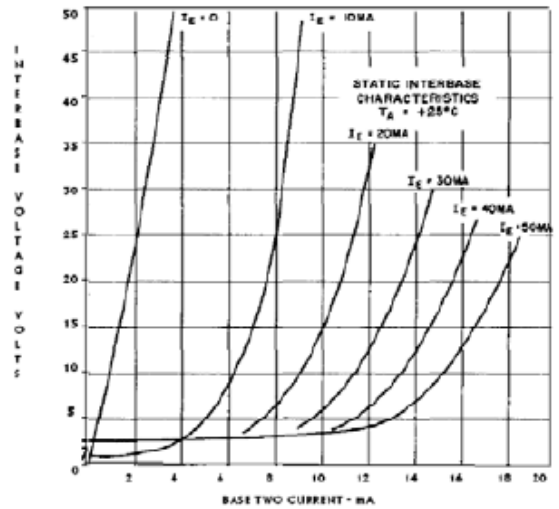
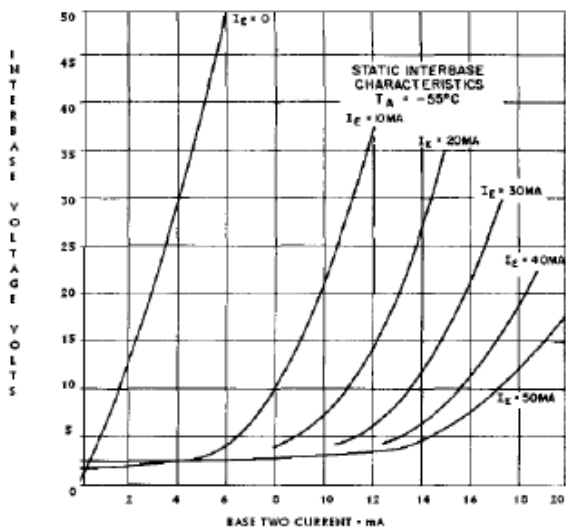
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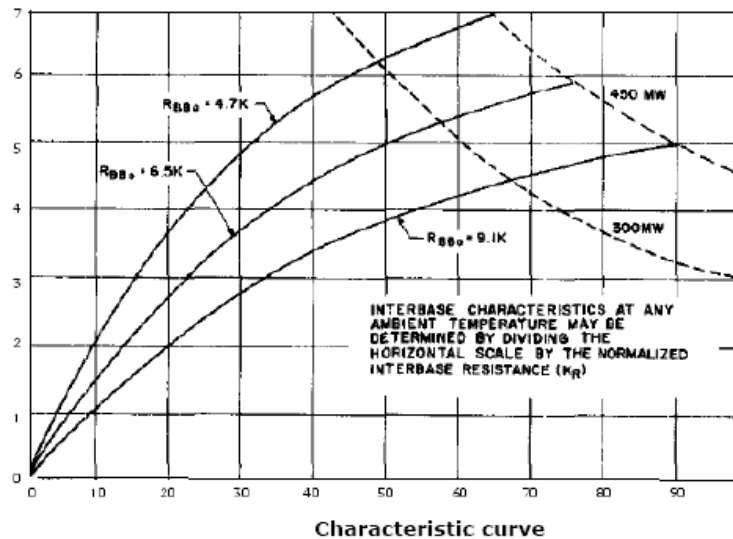
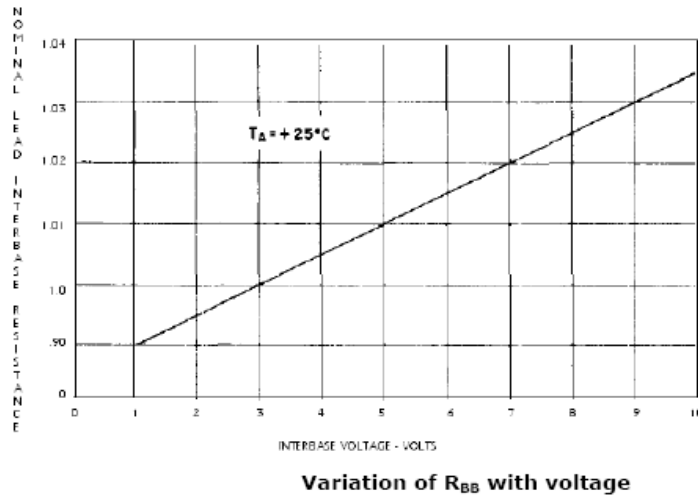
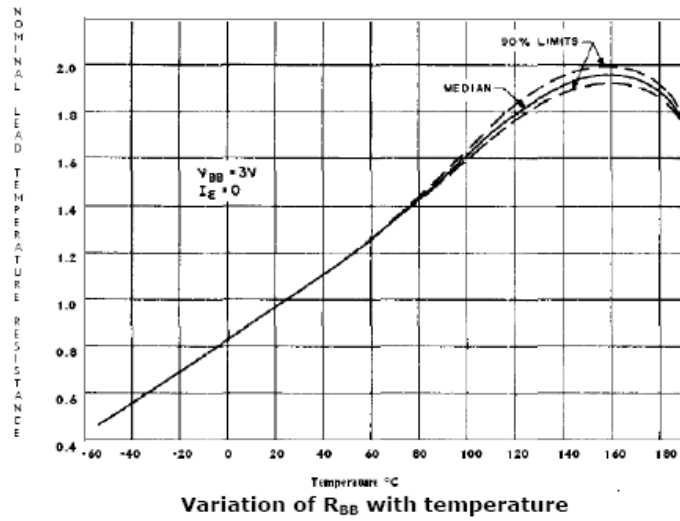
Static interbase characteristic curves showing important parameters and measurement points



Static emitter characteristics

# DIGITRON SEMICONDUCTORS

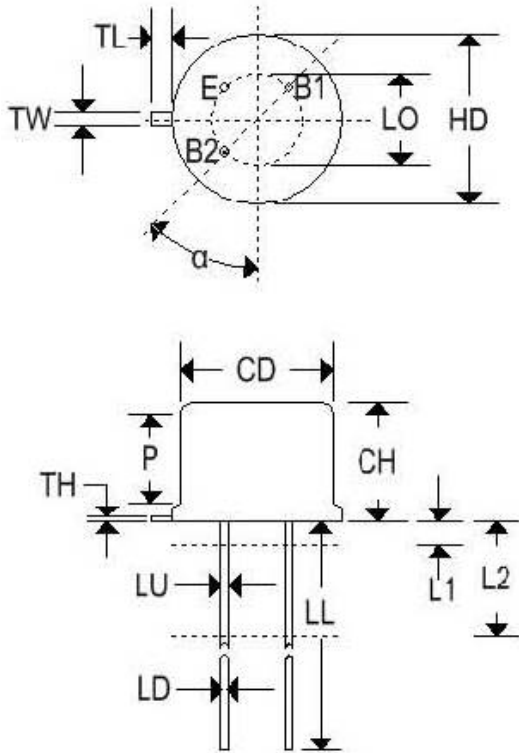
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Dim	TO-5			
	Inches		Millimeters	
	Min	Max	Min	Max
HD	0.335	0.370	8.510	9.400
CD	0.305	0.335	7.750	8.510
CH	0.240	0.260	6.100	6.600
LL	1.500	-	38.100	-
LD	0.016	0.021	0.410	0.530
LU	0.016	0.019	0.410	0.480
P	0.100	-	2.540	-
TL	0.029	0.045	0.740	1.140
TW	0.028	0.034	0.710	0.860
TH	0.009	0.125	0.230	3.180
LO	0.141 NOM		3.590 NOM	
$\alpha$	45°TP		45°TP	